

RELIABILITY REPORT
FOR
MAX1444EHJ+
PLASTIC ENCAPSULATED DEVICES

December 17, 2010

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.
SUNNYVALE, CA 94086

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| Approved by |
| Don Lipps |
| Quality Assurance |
| Manager, Reliability Engineering |

Conclusion

The MAX1444EHJ+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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I. Device Description

A. General

The MAX1444 10-bit, 3V analog-to-digital converter (ADC) features a pipelined 10-stage ADC architecture with fully differential wideband track-and-hold (T/H) input and digital error correction incorporating a fully differential signal path. This ADC is optimized for lowpower, high dynamic performance applications in imaging and digital communications. The MAX1444 operates from a single 2.7V to 3.6V supply, consuming only 57mW while delivering a 59.5dB signal-to-noise ratio (SNR) at a 20MHz input frequency. The fully differential input stage has a 400MHz -3dB bandwidth and may be operated with single-ended inputs. In addition to low operating power, the MAX1444 features a 5 μ A power-down mode for idle periods. An internal 2.048V precision bandgap reference is used to set the ADC full-scale range. A flexible reference structure allows the user to supply a buffered, direct, or externally derived reference for applications requiring increased accuracy or a different input voltage range. [See a parametric table of the complete family of pin-compatible, 10-bit high-speed ADCs.](#) The MAX1444 has parallel, offset binary, CMOS-compatible three-state outputs that can be operated from 1.7V to 3.6V to allow flexible interfacing. The device is available in a 5mm x 5mm 32-pin TQFP package and is specified over the extended industrial (-40°C to +85°C) temperature range.

II. Manufacturing Information

| | |
|----------------------------------|---|
| A. Description/Function: | 10-Bit, 40Msps, 3.0V, Low-Power ADC with Internal Reference |
| B. Process: | TS35 |
| C. Number of Device Transistors: | |
| D. Fabrication Location: | Taiwan |
| E. Assembly Location: | Philippines |
| F. Date of Initial Production: | July 22, 2000 |

III. Packaging Information

| | |
|--|--------------------------|
| A. Package Type: | 32-pin TQFP |
| B. Lead Frame: | Copper |
| C. Lead Finish: | 100% matte Tin |
| D. Die Attach: | Conductive |
| E. Bondwire: | Au (1 mil dia.) |
| F. Mold Material: | Epoxy with silica filler |
| G. Assembly Diagram: | #05-2101-0024 |
| H. Flammability Rating: | Class UL94-V0 |
| I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C | Level 1 |
| J. Single Layer Theta Ja: | N/A |
| K. Single Layer Theta Jc: | N/A |
| L. Multi Layer Theta Ja: | 53.5°C/W |
| M. Multi Layer Theta Jc: | N/A |

IV. Die Information

| | |
|----------------------------|---|
| A. Dimensions: | 85 X 87 mils |
| B. Passivation: | Si ₃ N ₄ /SiO ₂ (Silicon nitride/ Silicon dioxide) |
| C. Interconnect: | Al/0.5%Cu with Ti/TiN Barrier |
| D. Backside Metallization: | None |
| E. Minimum Metal Width: | 0.35μm F. |
| Minimum Metal Spacing: | 0.35μm |
| G. Bondpad Dimensions: | 5 mil. Sq. |
| H. Isolation Dielectric: | SiO ₂ |
| I. Die Separation Method: | Wafer Saw |

V. Quality Assurance Information

- A. Quality Assurance Contacts: Don Lipps (Manager, Reliability Engineering)
Bryan Preeshl (Vice President of QA)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 79 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 13.9 \times 10^{-9}$$

$\lambda = 13.9$ F.I.T. (60% confidence level @ 25°C)

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at <http://www.maxim-ic.com/qa/reliability/monitor>. Cumulative monitor data for the TS35 Process results in a FIT Rate of 0.11 @ 25C and 1.93 @ 55C (0.8 eV, 60% UCL)

B. Moisture Resistance Tests

The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

C. E.S.D. and Latch-Up Testing (lot K43AAQ002C, D/C 0047)

The AC12-3 die type has been found to have all pins able to withstand a HBM transient pulse of +/-1000V per Mil-Std 883 Method 3015.7. Latch-Up testing has shown that this device withstands a current of +/-250mA.

Table 1
Reliability Evaluation Test Results

MAX1444EHJ+

| TEST ITEM | TEST CONDITION | FAILURE IDENTIFICATION | SAMPLE SIZE | NUMBER OF FAILURES | COMMENTS |
|----------------------------------|---|----------------------------------|-------------|--------------------|----------------------|
| Static Life Test (Note 1) | Ta = 135°C Biased Time = 192 hrs. | DC Parameters & functionality | 79 | 0 | K43AAQ001M, D/C 0020 |

Note 1: Life Test Data may represent plastic DIP qualification lots.